Supporting Information

Enhanced Field Emission of Quasialigned 3C-SiC

Nanoarrays Alloyed with Tiny Co Nano-Tips

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Characterization of SiC nanostructures



Supplementary Figure S1. Schematic typical characterization of as-synthesized SiC nanowires without tiny Co heads (sample B). (a) Corresponding TEM image of SiC nanowire and (b) its tip. (c) Representative SAED pattern of the nanowire. (d) Typical EDS spectrum of top parts of the nanowire.



Supplementary Figure S2. Typical Raman spectrum of the carbon fabric and sample A and B grown on it.

In Supplementary Figure S2, we show Raman spectra for similar probe locations for the as-synthesized SiC nanowires. Raman peaks centered at 796 cm⁻¹ are characteristic of the TO mode, and the peaks located within the range 840–990 cm⁻¹ (~ 950 cm⁻¹) correspond to the LO mode.^[1–3] It should be noted this broad amorphous bulge also arises from the Raman peak of amorphous SiO₂^[1, 2, 4] and the random stacking sequences of atomic planes, which create a virtual local mixture of polytypes, leading to the observation of additional peaks in the Raman spectrum. The 1355 cm⁻¹ is attributed to the Raman peak of carbon fabric.^[2]

References

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